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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE		Application No.	10/024,475
		Filing Date	December 21, 2001
		First Named Inventor	Chan-ho PARK
		Group Art Unit	2811
		Examiner Name	Ori Nadav
		Attorney Docket No.	1751-294
<i>Title of the Invention:</i> HIGH VOLTAGE SEMICONDUCTOR DEVICE HAVING HIGH BREAKDOWN VOLTAGE AND METHOD OF FABRICATING THE SAME			

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RESPONSE TO RESTRICTION REQUIREMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the restriction requirement mailed August 23, 2002, Applicant hereby elects Group I, consisting of claims 1-3, drawn to a semiconductor device, classified in class 257, subclass 341. Applicant reserves the right to pursue the non-elected claims in a divisional application.

Favorable action on the elected claims is earnestly solicited.

RESPECTFULLY SUBMITTED,					
NAME AND REG. NUMBER	Monica S. Davis, Registration No. 44,492				
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